



➤ Gallium Antimonide (GaSb) Substrate

Gallium Antimonide (GaSb) Substrate, is a compound material foamed by high purity Gallium and Antimony elements, grown by Liquid Encapsulated Czochralski (LEC) or Vertical Gradient Freeze (VGF) method. Thanks to its high mobility, it is widely being used in the fabrication of microwave device or laser components in regards of Microelectronic & Optoelectronics industry. 2" 3" and 4" are available to supply.



No.	Items	Standard Specifications		
1	Size	2"	3"	4"
2	Diameter mm	50.5±0.5	76.2±0.5	100±0.5
3	Growth Method	LEC	LEC	LEC
4	Conductivity	P/(Zn-doped or un-doped), N/Te-doped		
5	Orientation	(100)±0.5°, (111)±0.5°		
6	Thickness μm	500±25	600±25	800±25
7	Orientation Flat mm	16±2	22±1	32.5±1
8	Identification Flat mm	8±1	11±1	18±1
9	Mobility cm ² /v.s	200-3500 or as required		
10	Carrier Concentration cm ⁻³	(1-100)E17 or as required		
11	TTV μm max	15	15	15
12	Bow μm max	15	15	15
13	Warp μm max	20	20	20
14	Dislocation Density cm ⁻² max	500	1000	2000
15	Surface Finish	P/E, P/P	P/E, P/P	P/E, P/P
16	Packing	Single wafer container sealed in Aluminum bag.		

➤ Indium Arsenide (InAs) Substrate

Indium Arsenide (InAs) Substrate is compound by high purity Indium and Arsenic elements, grown by Liquid Encapsulated Czochralski (LEC) method. Thanks to its high hall mobility, it can be widely used as the substrate during the fabrication of InAsSb, InAsPSb or InNASb heterogeneous materials, or the infrared emitting devices between 2-14μm wave range. 2" 3" 4" can be supplied.



No.	Items	Standard Specifications		
1	Size	2"	3"	4"
2	Diameter mm	50.5±0.5	76.2±0.5	100±0.5
3	Growth Method	LEC	LEC	LEC
4	Conductivity	P/Zn-doped, N/(Sn/S-doped or un-doped)		
5	Orientation	(100)±0.5°, (111)±0.5°		
6	Thickness μm	500±25	600±25	800±25
7	Orientation Flat mm	16±2	22±2	32±2
8	Identification Flat mm	8±1	11±1	18±1
9	Mobility cm ² /v.s	60-300, ≥2000 or as required		
10	Carrier Concentration cm ⁻³	(3-80)E17 or ≤5E16		
11	TTV μm max	10	10	10
12	Bow μm max	10	10	10
13	Warp μm max	15	15	15
14	Dislocation Density cm ⁻² max	1000	2000	5000
15	Surface Finish	P/E, P/P	P/E, P/P	P/E, P/P
16	Packing	Single wafer container sealed in Aluminum bag.		